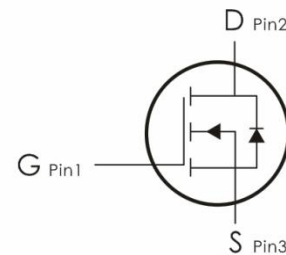
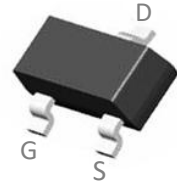


Description:

This N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge. It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=20V, I_D=2.8A, R_{DS(ON)} < 55m\ \Omega @ V_{GS}=4.5V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.



Absolute Maximum Ratings: ($T_A=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current- $T_A=25^\circ C$	2.8	A
	Continuous Drain Current- $T_A=100^\circ C$	2	
I_{DM}	Pulse Drain Current Tested ¹	12	A
P_D	Power Dissipation- $T_A=25^\circ C$	0.77	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	162	$^\circ C/W$

Package Marking and Ordering Information:

Part NO.	Marking	Package
DO2302E-Q	A2SHB:	SOT-23

Electrical Characteristics: ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\ \mu\text{A}$	20	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=19V$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 12V, V_{DS}=0A$	---	---	± 100	nA
On Characteristics						
$V_{GS(th)}$	GATE-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\ \mu\text{A}$	0.4	0.7	1	V
$R_{DS(on)}$	Drain-Source On-Resistance ²	$V_{GS}=4.5V, I_D=2.8A$	---	45	55	m Ω
		$V_{GS}=2.5V, I_D=2A$	---	62	85	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=10V, V_{GS}=0V, f=1\text{MHz}$	---	180	---	pF
C_{oss}	Output Capacitance		---	35	---	
C_{rss}	Reverse Transfer Capacitance		---	25	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DS}=10V, V_{GS}=4.5V,$ $I_D=2.8A, R_{GEN}=3\ \Omega$	---	2.3	---	ns
t_r	Rise Time		---	3.1	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	9.2	---	ns
t_f	Fall Time		---	2.5	---	ns
Q_g	Total Gate Charge	$V_{GS}=4.5V, V_{DS}=10V,$ $I_D=2.8A$	---	2.7	---	nC
Q_{gs}	Gate-Source Charge		---	0.4	---	nC
Q_{gd}	Gate-Drain "Miller" Charge		---	0.5	---	nC
Drain-Source Diode Characteristics						
I_S	Continuous Source Current	$V_G=V_D=0V$	---	---	2.8	A
I_{SM}	Pulsed Source Current	$V_G=V_D=0V$	---	---	12	A

V_{SD}	Forward Voltage	V _{GS} =0V, I _S =2.8A	---	---	1.2	V
-----------------------	-----------------	---	-----	-----	-----	---

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 0.5%

Typical Characteristics: (T_C=25°C unless otherwise noted)

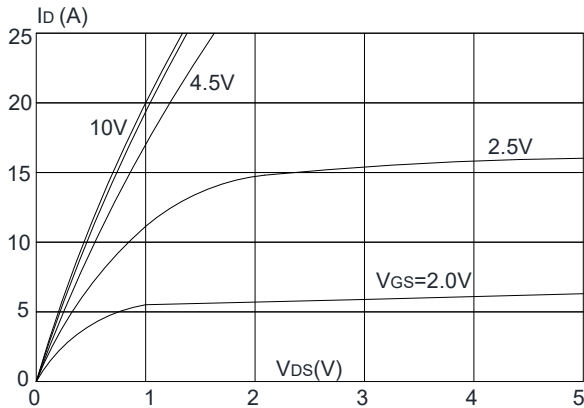


Figure 1: Output Characteristics

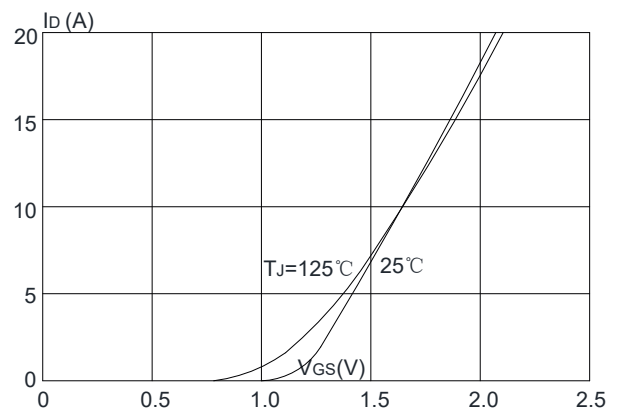


Figure 2: Typical Transfer Characteristics

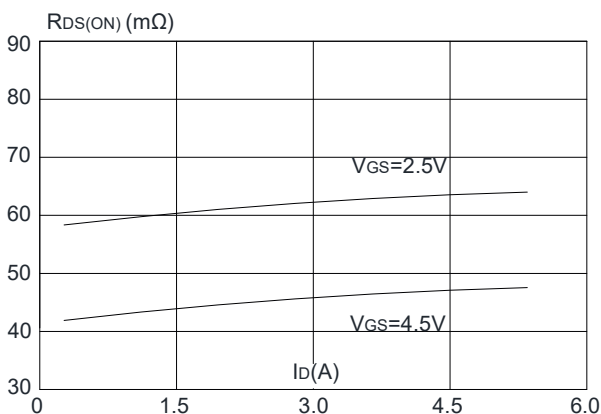


Figure 3: On-resistance vs. Drain Current

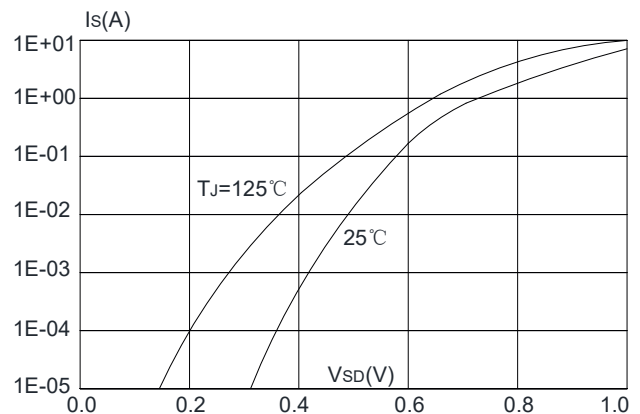


Figure 4: Body Diode Characteristics

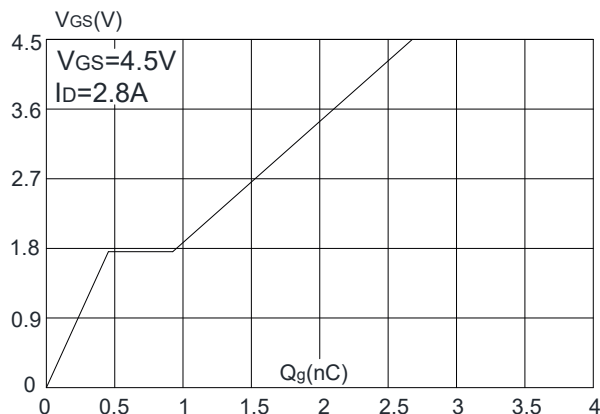


Figure 5: Gate Charge Characteristics

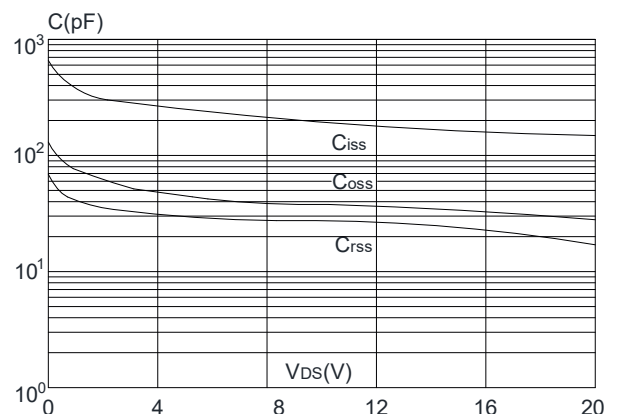


Figure 6: Capacitance Characteristics

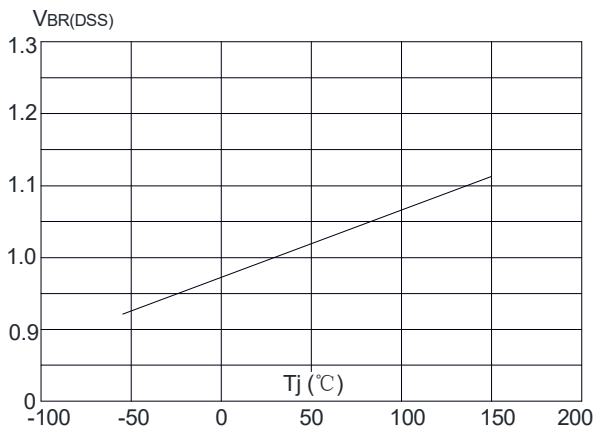


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

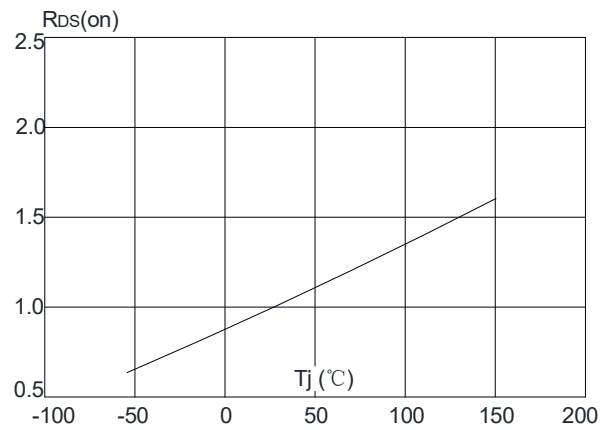


Figure 8: Normalized on Resistance vs. Junction Temperature

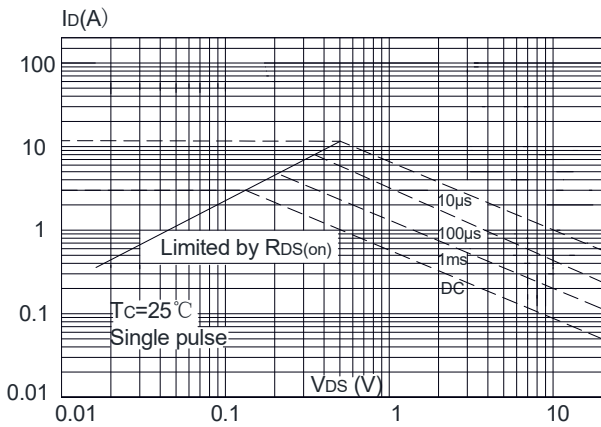


Figure 9: Maximum Safe Operating Area

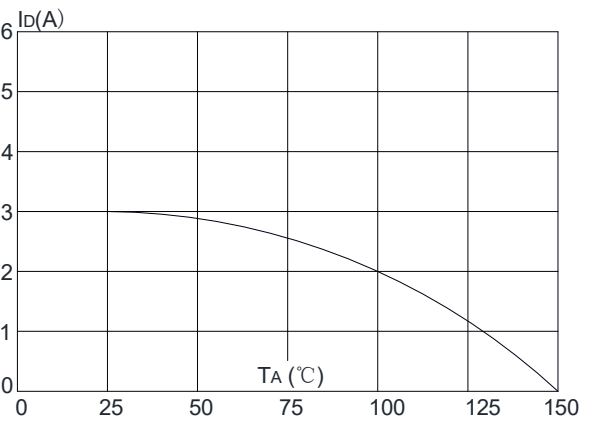


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

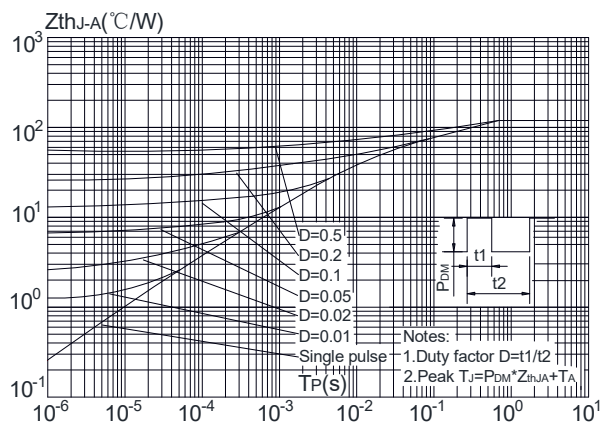


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient